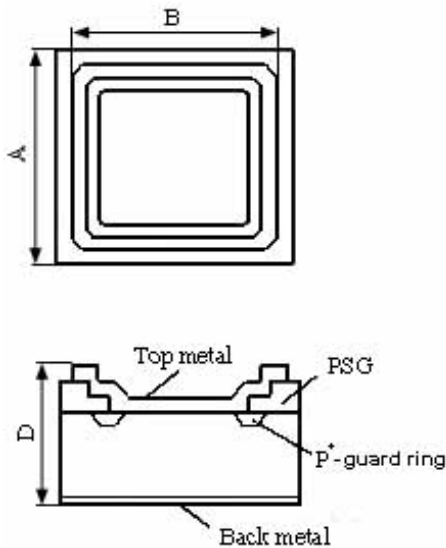




2A/60V. Die Size-51mil.

Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	V_{BR}	V	60	65
Average Rectified Forward Current	$I_{F(AV)}$	A	2,0	-
DC Forward Voltage @ 25°C, $I_F=2,0\text{A}$	V_F	V	0,72	0,70
Maximum Reverse Current @ 25°C, $V_R=60\text{V}$ @ 125°C, $V_R=60\text{V}$	I_R	mA	0,010 10,0	0,008 8,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	60	-
Peak Repetitive Reverse Surge Current @ 2,0µs, f=1kHz., $T_J<175^\circ\text{C}$.	I_{RRM}	A	2,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	V_{ESD}	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	°C	175	



DIM	ITEM	µm
A _x	Wafer Form Die Size	1300
A _y		1300
B _x	Top Metal Size	1160
B _y		1160
D	Thickness	300max.
Scribe line Width		80

Top metal:
 a) **Al-Ni-Ag** – for Soldering;
 b) **Al** – for Wire Bonding.
 Backside metal: **Ti-Ni-Ag**.